



US005500537A

United States Patent

[19]

Tsumura et al.**Patent Number:** **5,500,537****Date of Patent:** **Mar. 19, 1996**

[54] **FIELD-EFFECT TRANSISTOR WITH AT LEAST TWO DIFFERENT SEMICONDUCTIVE ORGANIC CHANNEL COMPOUNDS**

[75] Inventors: **Akira Tsumura; Hiroyuki Fuchigami; Hideharu Nobutoki; Hiroshi Koezuka,** all of Amagasaki, Japan

[73] Assignee: **Mitsubishi Denki Kabushiki Kaisha,** Tokyo, Japan

[21] Appl. No.: **372,219**

[22] Filed: **Jul. 30, 1993**

Related U.S. Application Data

[63] Continuation of Ser. No. 785,163, Oct. 31, 1991, abandoned, which is a continuation of Ser. No. 562,561, Aug. 3, 1990, abandoned.

Foreign Application Priority Data

Aug. 17, 1989	[JP]	Japan	1-211739
Aug. 17, 1989	[JP]	Japan	1-211740
Jan. 29, 1990	[JP]	Japan	2-19464
Jun. 19, 1990	[JP]	Japan	2-160629

[51] Int. Cl.⁶ **H01L 35/24; H01L 51/00**

[52] U.S. Cl. **257/40; 257/20; 257/24;**
..... **257/191; 257/192**

[58] Field of Search **357/8, 16; 350/334;**
..... **257/40, 20, 24, 191, 192**

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Primary Examiner—Sara W. Crane

Assistant Examiner—Alice W. Tang

Attorney, Agent, or Firm—Oblon, Spivak, McClelland, Maier & Neustadt

[57]

ABSTRACT

A field effect transistor has a channel between a source electrode and a drain electrode made from an organic semiconductor. In one form of the invention, the channel is a mixture of at least two different organic compounds. In another form of the invention, the channel is a lamination of at least two films of different organic compounds. The channel can also be a π -conjugated block copolymer of at least two different types of monomers.

14 Claims, 3 Drawing Sheets

